L	Hits	Search Text	DB	Time stamp
Number				
-	213204	257/\$3.ccls. or 438/\$3.ccls.	USPAT; EPO; JPO; DERWENT	2003/07/01 14:45
-	6	(257/\$3.ccls. or 438/\$3.ccls.) and insulat\$3 and radiat\$3 and (amorphous	USPAT; EPO; JPO;	2002/04/09 09:46
	1	near2 silicon) and crystall\$7 and explosive (257/\$3.ccls. or 438/\$3.ccls.) and (xcr	DERWENT USPAT;	2002/04/09
	_	or (explosive adj recrystallization)) and irradiat\$3 and dopant and gate	EPO; JPO; DERWENT	09:58
-	103	(257/\$3.ccls. or 438/\$3.ccls.) and recrystallization and irradiat\$3 and	USPAT; EPO; JPO;	2002/04/09 09:59
-	85	dopant and gate ((257/\$3.ccls.) and recrystallization and irradiat\$3 and	DERWENT USPAT; EPO; JPO;	2002/04/09 15:19
		dopant and gate) and (amorphous adj silicon)	DERWENT	2002/04/02
-	3	mosfet same (laser or irradiate) same amorphous same (dopant or dope)	USPAT; EPO; JPO; DERWENT	2002/04/09
_	111	(laser or irradiate) same (amorphous adj silicon) same (dopant or dope)	USPAT; EPO; JPO; DERWENT	2002/04/10 16:52
-	10	((laser or irradiate) same (amorphous adj silicon) same (dopant or dope)) same	USPAT; EPO; JPO;	2002/04/09 16:14
_	241	(insulat\$4 adj layer) mosfet with laser	DERWENT USPAT; EPO; JPO;	2002/04/09
	2	(mosfet with laser) same (amorphous adj silicon)	DERWENT USPAT; EPO; JPO;	2002/04/09
_	. 12	(mosfet with laser) same (dope dopant	DERWENT USPAT;	2002/04/09
_	42	doped) (mosfet with laser) and ((dope dopant	EPO; JPO; DERWENT USPAT;	2002/04/09
_	12557	doped) with gate) (mosfet or fet or mos) same dop\$3 same	EPO; JPO; DERWENT USPAT;	18:07
		gate	EPO; JPO; DERWENT	17:18
_	158	((mosfet or fet or mos) same dop\$3 same gate) same (laser or irradiation)	USPAT; EPO; JPO; DERWENT	2002/04/10
-	4	"5966605"	USPAT; EPO; JPO; DERWENT	2002/04/10 11:07
-	54793	gate with silicon	USPAT; EPO; JPO;	2002/04/10 14:12
-	6957	((mosfet or fet or mos) same dop\$3 same gate) and (gate with silicon)	DERWENT USPAT; EPO; JPO;	2002/04/10 14:12
_	15744	gate near2 silicon	DERWENT USPAT; EPO; JPO;	2002/04/10 14:12
-	2731	((mosfet or fet or mos) same dop\$3 same gate) and (gate near2 silicon)	DERWENT USPAT; EPO; JPO;	2002/04/10
-	234	(((mosfet or fet or mos) same dop\$3 same	DERWENT USPAT;	2002/04/10
_	110	<pre>gate) and (gate near2 silicon)) and (laser or irradiate) ((((mosfet or fet or mos) same dop\$3 same</pre>	EPO; JPO; DERWENT USPAT;	14:15
		gate) and (gate near2 silicon)) and (laser or irradiate)) and amorphous and (recrystallize or polycrystalline or	EPO; JPO; DERWENT	16:15
		crystalline)		

-	13	"5937325"	USPAT;	2002/04/10
			EPO; JPO;	16:19
			DERWENT	
l -	8	"6013928"	USPAT;	2002/04/10
		0010310	EPO; JPO;	16:20
			DERWENT	1 10.20
		43		0000/04/10
-	34	(laser or irradiate) same (amorphous adj	USPAT;	2002/04/10
		silicon) same ((dopant or dope) and	EPO; JPO;	16:53
		(sputter or deposition or evaporation))	DERWENT	
-	3488	(mosfet or fet or mos) same dop\$3 same	USPAT;	2002/04/10
		gate same (sputter or evaporat\$3 or	EPO; JPO;	17:20
		deposit\$3)	DERWENT	
_	3958	((mosfet or fet or mos) same dop\$3 same	USPAT;	2002/04/10
] 3,30	gate) and (dop\$3 with (sputter or	EPO; JPO;	17:21
			DERWENT	17.21
	1 2 7	deposit\$3 or evaporat\$3))		2002/04/10
-	137		USPAT;	2002/04/10
		gate) and (dop\$3 with (sputter or	EPO; JPO;	17:21
		evaporat\$3))	DERWENT	
-	41	((mosfet or fet or mos) same dop\$3 same	USPAT;	2002/04/10
		gate) same (dop\$3 with (sputter or	EPO; JPO;	17:25
	·	evaporat\$3))	DERWENT	
_	75	((mosfet or fet or mos) same dop\$3 same	USPAT;	2002/04/10
	'3	gate) same (dop\$3 with (sputter\$3 or	EPO; JPO;	17:32
		evaporat\$3))	DERWENT	
	220		USPAT;	2002/04/10
-	320	(dop\$3 with (sputter\$3 or evaporat\$3)		17:46
		with silicon) and (mos or fet or mosfet)	EPO; JPO;	1/:40
			DERWENT	0000/61/50
-	35	(dop\$3 with (sputter\$3 or evaporat\$3)	USPAT;	2002/04/10
		with silicon) same (mos or fet or mosfet)	EPO; JPO;	17:35
	}		DERWENT	
-	28	(dop\$3 with (sputter\$3 or evaporat\$3)	USPAT;	2002/04/10
		with silicon) same laser	EPO; JPO;	17:51
		·	DERWENT	
_	190	(dop\$3 with (sputter\$3 or evaporat\$3))	USPAT;	2002/04/10
		same laser	EPO; JPO;	18:02
1]		DERWENT	
_	2	"6165875"	USPAT;	2002/04/10
_		0103073	EPO; JPO;	18:02
	İ		DERWENT	10.02
	0040			2002/04/11
-	2848	gate with (metal or cap or capped) with	USPAT;	16:14
		(tungsten or tantalum or titanium or	EPO; JPO;	10:14
		platinum)	DERWENT	2002/04/33
-	331	(gate with (metal or cap or capped) with	USPAT;	2002/04/11
		(tungsten or tantalum or titanium or	EPO; JPO;	16:20
	1	platinum)) and laser	DERWENT	
-	89		USPAT;	2002/04/11
1		(tungsten or tantalum or titanium or	EPO; JPO;	16:20
	1	platinum)) and laser and mosfet	DERWENT	
_	۵	"6077758"	USPAT;	2002/04/11
	1	00,7700	JPO;	17:34
	1		DERWENT	*'53
	11000	(hauan au imdina au anani =		2002/04/15
-	11867	(boron or indium or arsenic or	USPAT;	2002/04/15
	1	phosphorus) with (sputter\$3 or CVD or	EPO; JPO;	14:06
1		evaporat\$3)	DERWENT	
-	12	((boron or indium or arsenic or	USPAT;	2002/04/15
	1	phosphorus) with (sputter\$3 or CVD or	EPO; JPO;	14:02
	1	evaporat\$3)) same dopant same laser	DERWENT	
-	1098	((boron or indium or arsenic or	USPAT;	2002/04/15
1	1	phosphorus) near2 layer) with (sputter\$3	EPO; JPO;	15:10
	1	or CVD or evaporat\$3)	DERWENT	
_	33	(((boron or indium or arsenic or	USPAT;	2002/04/15
		phosphorus) near2 layer) with (sputter\$3	EPO; JPO;	14:09
1	1	or CVD or evaporat\$3)) same dopant	DERWENT	
1_	239	((boron or indium or arsenic or	USPAT;	2002/04/15
	239	phosphorus) near2 layer) with (sputter\$3	EPO; JPO;	15:13
	1		DERWENT	13.13
_	4.5	or CVD or evaporat\$3) with surface		2002/04/15
-	46	(((boron or indium or arsenic or	USPAT;	2002/04/15
	1	phosphorus) near2 layer) with (sputter\$3	EPO; JPO;	15:14
		or CVD or evaporat\$3) with surface) and	DERWENT	1
		laser	l	<u> </u>

-	2	5966605.pn.	USPAT;	2002/09/13
			EPO; JPO;	13:14
			DERWENT	
-	2	6365476.pn.	USPAT;	2002/09/13
ŀ			EPO; JPO;	13:15
			DERWENT	
l _	2	6274488.pn.	USPAT;	2002/09/13
		02/1100.pii.	EPO; JPO;	13:16
]				13.10
1	ا م	6077760	DERWENT	0000/00/10
	2	6077758.pn.	USPAT;	2002/09/13
			EPO; JPO;	13:16
			DERWENT	
-	1175		USPAT;	2002/12/08
		dop\$3 and crystalliz\$5	EPO; JPO;	12:17
		-	DERWENT	
_	34	radiat\$3 same amorphous same silicon same	USPAT;	2002/12/08
	•	dop\$3 same crystalliz\$5	EPO; JPO;	12:12
		dopps same orystallizes	DERWENT	12:12
	1 12	/w-dish02 same amaumbawa same ailiman		2002/12/09
-	12	(radiat\$3 same amorphous same silicon	USPAT;	2002/12/08
		same dop\$3 same crystalliz\$5) same gate	EPO; JPO;	12:12
			DERWENT	
-	350	radiat\$3 and amorphous and silicon and	USPAT;	2002/12/08
		dop\$3 and crystalliz\$5 and (gate with	EPO; JPO;	12:22
		dop\$3)	DERWENT	
-	315	(radiat\$3 and amorphous and silicon and	USPAT;	2002/12/08
		dop\$3 and crystalliz\$5 and (gate with	EPO; JPO;	12:20
		dop\$3)) and laser	DERWENT	
	181		USPAT;	2002/12/08
_	101			1
		dop\$3 and crystalliz\$5 and (gate with	EPO; JPO;	12:21
		dop\$3)) and laser) and 438/\$3.ccls.	DERWENT	
-	181		USPAT;	2002/12/08
		dop\$3 and crystalliz\$5 and (gate with	EPO; JPO;	12:21
		dop\$3)) and laser) and 438/\$3.ccls.) and	DERWENT	1
		@ad<20010829		
l <u>-</u>	33	radiat\$3 and amorphous and silicon and	USPAT;	2002/12/08
		dop\$3 and crystalliz\$5 and (gate with	EPO; JPO;	12:59
		dop\$3 with amorphous)	DERWENT	
	4		USPAT;	2002/12/08
_	4		EPO; JPO;	13:04
		dop\$3 with amorphous)		13.04
		11 . 40	DERWENT	2002/12/00
-	2	radiat\$3 same amorphous same	USPAT;	2002/12/08
		(crystalliz\$5 with gate with dop\$3)	EPO; JPO;	13:08
			DERWENT	
-	11	radiat\$3 same amorphous same crystalliz\$5	USPAT;	2002/12/08
		same (gate with dop\$3)	EPO; JPO;	13:30
		-	DERWENT	
-	28	anneal\$3 same crystalliz\$5 same	USPAT;	2002/12/08
		(amorphous with gate with dop\$3)	EPO; JPO;	15:51
		/	DERWENT	
_	3	("5872761" "5994179" "6054355").PN.	USPAT	2002/12/08
	3	(30/2/01 33941/3 0034333 .PN.	VOLAL	14:00
	1.7	water with haight with "EAA" with	IICDAM -	2002/12/08
-	11	gate with height with "500" with	USPAT;	1 ' '
		(nanometer\$1 or nm)	EPO; JPO;	15:55
			DERWENT	
-	62	gate with height with ("400" or "300" or	USPAT;	2002/12/08
		"200" or "100") with (nanometer\$1 or nm)	EPO; JPO;	15:56
			DERWENT	
-	2	6159782.pn.	USPAT;	2003/06/03
		•	EPO; JPO;	14:19
			DERWENT	'
_	144	xcr or (explosive adj \$2crystalliz\$4)	USPAT;	2003/06/30
	144	YOU OF (EVELOUINE and Archargments)	US-PGPUB;	15:59
			t	13.39
			EPO; JPO;	
	_		DERWENT	0000 (05 (55
-	0	(xcr or (explosive adj \$2crystalliz\$4))	USPAT;	2003/06/30
		and (laser same amorphous same	US-PGPUB;	15:57
		(polycrystalline or polysilicon))	EPO; JPO;	1
			DERWENT	
		· · · · · · · · · · · · · · · · · · ·		

	107	0.1400010000		0000/06/00
-	127	xcr and @ad<20010829	USPAT;	2003/06/30
			US-PGPUB;	16:00
			EPO; JPO;	
	ا ا	4 1.0 1.00010000 1.1	DERWENT	2002/06/20
-	0	(xcr and @ad<20010829) and laser and	USPAT;	2003/06/30
		amorphous and (polycrystalline or	US-PGPUB;	15:58
		polysilicon) and (dopant or boron)	EPO; JPO;	i i
İ	100		DERWENT	0000106100
-	138	xcr	USPAT;	2003/06/30
			US-PGPUB;	15:58
			EPO; JPO;	
		/	DERWENT	2002/06/20
-	0	(xcr and @ad<20010829) and 438/\$3.ccls.	USPAT;	2003/06/30
			US-PGPUB;	15:59
			EPO; JPO; DERWENT	
				2003/06/30
-	6	explosive adj \$2crystalliz\$4	USPAT;	15:59
			US-PGPUB;	12:29
			EPO; JPO;	
1	35	explosive adj \$2crystalliz\$5	DERWENT USPAT;	2003/06/30
-	35	explosive adj \$2Crystalil2\$5		15:59
			US-PGPUB; EPO; JPO;	15.55
			DERWENT	
	16	/ownlosive add clammatallizes) and	USPAT;	2003/06/30
-	16	(explosive adj \$2crystalliz\$5) and 438/\$3.ccls.	US-PGPUB;	16:42
		730/ Y3.CC13.	EPO; JPO;	10.32
1			DERWENT	
_	15	((explosive adj \$2crystalliz\$5) and	USPAT;	2003/06/30
i -	15	438/\$3.ccls.) and @ad<20010829	US-PGPUB;	17:46
		,	EPO; JPO;	
			DERWENT	
_	18	("4522845" "4622735" "4683645"	USPAT	2003/06/30
	"	"4830971" "4924294" "4931353"		16:02
1		"5010032" "5122479" "5236865"		
		"5302538" "5405806" "5563100"		
		"5593923" "5888888" "6060392"		
		"6072222" "6174774" "6274488").PN.		
-	10	("4151008" "4456490" "4617066"	USPAT	2003/06/30
1		"5756369" "5897381" "5908307"		16:10
	1	"5923963" "5989966" "6153483"		
	1	"6188106").PN.		0000 (05 (00
-	17	("4522845" "4622735" "4683645"	USPAT	2003/06/30
		"4830971" "4924294" "4931353"		16:23
		"5010032" "5122479" "5236865"	ļ	
		"5302538" "5405806" "5563100"		
1		"5593923" "5888888" "6060392"		
		"6072222" "6174774").PN.	USPAT;	2003/06/30
-	646	laser same gate same dop\$3 same silicon	US-PGPUB;	16:40
			EPO; JPO;	100
1			DERWENT	
_	277	(laser same gate same dop\$3 same silicon)	USPAT;	2003/06/30
1	""	same amorphous	US-PGPUB;	16:41
1		- Control of the Cont	EPO; JPO;	
1			DERWENT	ł l
-	80	((laser same gate same dop\$3 same	USPAT;	2003/06/30
		silicon) same amorphous) same temperature	US-PGPUB;	16:41
1		•	EPO; JPO;	
1	1		DERWENT	
-	74	(((laser same gate same dop\$3 same	USPAT;	2003/06/30
		silicon) same amorphous) same	US-PGPUB;	17:51
		temperature) and @ad<20010829	EPO; JPO;	
			DERWENT	0000/06/00
-	41	((((laser same gate same dop\$3 same	USPAT;	2003/06/30
		silicon) same amorphous) same	US-PGPUB;	17:43
		temperature) and @ad<20010829) and	EPO; JPO;	
		438/\$3.ccls.	DERWENT	

-	169	melting with temperature with amorphous with silicon	USPAT; US-PGPUB; EPO; JPO;	2003/06/30
-	7		DERWENT USPAT	2003/06/30
	_	"5966605" "5998272" "6225176" "6297115").PN.		17:29
_	3	laser same silicon same amorphous same wavelength same (pulse adj width) same (irradiance or fluence) same (repetition adj rate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 17:45
_	19	,	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 17:50
_	12	width) same (irradiance or fluence) same (repetition adj rate)) and @ad<20010829	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30
-	10	((laser same wavelength same (pulse adj width) same (irradiance or fluence) same (repetition adj rate)) and @ad<20010829) not ultratech	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30
_	293	laser and wavelength and (pulse adj width) and (irradiance or fluence) and (repetition adj rate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30
-	0	((((laser same gate same dop\$3 same silicon) same amorphous) same temperature) and @ad<20010829) and (laser and wavelength and (pulse adj width) and (irradiance or fluence) and (repetition adj rate))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 17:51
-	1	1	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 17:52
_	1	<pre>(melting with temperature with amorphous with silicon) and (laser and wavelength and (pulse adj width) and (irradiance or fluence) and (repetition adj rate))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30
_	7	(laser and wavelength and (pulse adj width) and (irradiance or fluence) and (repetition adj rate)) and (dopant or impurity) and amorphous and silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30
_	1416	diffus\$3 same amorphous same dop\$3 same silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 18:19
_	83	(diffus\$3 same amorphous same dop\$3 same silicon) same laser	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 18:19
-	1	(laser and wavelength and (pulse adj width) and (irradiance or fluence) and (repetition adj rate)) and ((diffus\$3 same amorphous same dop\$3 same silicon) same laser)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30
-	72	((diffus\$3 same amorphous same dop\$3 same silicon) same laser) and @ad<20010829	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 18:21
-	31	((diffus\$3 same amorphous same dop\$3 same silicon) same laser) same gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 18:21
-	28	(((diffus\$3 same amorphous same dop\$3 same silicon) same laser) same gate) and @ad<20010829	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30

-	1	(dopant adj layer) with top with	USPAT;	2003/06/30
		(amorphous adj silicon)	US-PGPUB;	19:19
		,	EPO; JPO;	
			DERWENT	
_	307	laser with (amorphous adj silicon) with	USPAT;	2003/06/30
		(dop\$3 or impurity)	US-PGPUB;	19:20
			EPO; JPO;	
			DERWENT	
-	70	(laser with (amorphous adj silicon) with	USPAT;	2003/06/30
		(dop\$3 or impurity)) with gate	US-PGPUB;	19:20
		-	EPO; JPO;	
			DERWENT	
-	13	((laser with (amorphous adj silicon) with	USPAT;	2003/06/30
		(dop\$3 or impurity)) with gate) same	US-PGPUB;	19:21
	}	temperature	EPO; JPO;	
			DERWENT	
-	2	5908307.pn.	USPAT;	2003/07/01
	,		US-PGPUB;	15:08
			EPO; JPO;	
			DERWENT	
-	4	,	USPAT;	2003/07/01
		width) same (irradiance or fluence)	US-PGPUB;	15:10
			EPO; JPO;	
			DERWENT	2002/07/01
-	10	(wavelength same (pulse adj width) same	USPAT;	2003/07/01
		(irradiance or fluence)) and (melt\$3 with	US-PGPUB;	15:10
		silicon)	EPO; JPO; DERWENT	
	100		USPAT;	2003/07/01
_	129	wavelength same (pulse adj width) same	US-PGPUB;	15:14
		(irradiance or fluence)	EPO; JPO;	13.13
			DERWENT	
	1		I DULAMENT	I